

DZ2J360×0L

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: JG or JR

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±8	kV
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) *1 Mounted on glass epoxy print board (45 mm × 45 mm × 1 mm)

Solder in (Recommended land pattern)

*2 Test method : IEC61000_4_2

(C = 150 pF, R = 330 Ω, Contact discharge : 10 times)

■ Electrical Characteristics $T_a = 25\text{ }^\circ\text{C} \pm 3\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 10 mA			1.0	V
Zener voltage ^{*1, *2}	V _Z	I _Z = 2 mA	34.20		37.80	V
Zener operating resistance	R _Z	I _Z = 2 mA			250	Ω
Zener rise operating resistance	R _{ZK}	I _Z = 0.5 mA			250	Ω
Reverse current	I _R	V _R = 27 V			0.05	μA
Temperature coefficient of zener voltage ^{*3}	SZ	I _Z = 2 mA		35.4		mV/°C

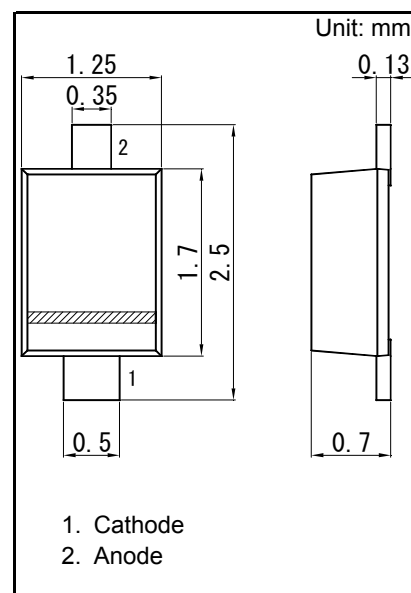
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

3. *1 The temperature must be controlled 25 °C for V_Z measurement.V_Z value measured at other temperature must be adjusted to V_Z (25 °C).*2 V_Z guaranteed 20 ms after current flow*3 T_j = 25 °C to 150 °C

Rank classification

Code	M	O
Rank	M	No-rank
V _Z	35.10 to 36.90	34.20 to 37.80
Marking symbol	JR	JG



1. Cathode
2. Anode

Panasonic	SMini2-F5-B
JEITA	SC-90A
Code	—

Internal Connection

